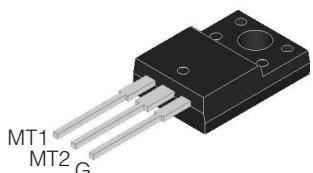
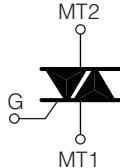


STANDARD TRIAC

| | |
|---|--|
| <p>TO220-F (FULLY ISOLATED CASE)</p>   | <p>On-State Current 16 Amp</p> <p>Gate Trigger Current ≤ 100 mA</p> <p>Off-State Voltage 200 V ÷ 800 V</p> <p>This series of TRIACs uses a high performance PNPN technology. These parts are intended for general purpose AC switching applications with highly inductive loads.</p> |
|---|--|

Absolute Maximum Ratings, according to IEC publication No. 134

| SYMBOL | PARAMETER | CONDITIONS | Value | Unit |
|--------------|---|--|------------|-----------|
| $I_{T(RMS)}$ | RMS On-state Current (full sine wave) | All Conduction Angle, $T_c = 95$ °C | 16 | A |
| I_{TSM} | Non-repetitive On-State Current | Full Cycle, 60 Hz ($t = 16.7$ ms) | 176 | A |
| I_{TSM} | Non-repetitive On-State Current | Full Cycle, 50 Hz ($t = 20$ ms) | 160 | A |
| I^2t | Fusing Current | $t_p = 10$ ms, Half Cycle | 128 | A^2s |
| I_{GM} | Peak Gate Current | $20 \mu s$ max. $T_j = 125$ °C | 4 | A |
| $P_{G(AV)}$ | Average Gate Power Dissipation | $T_j = 125$ °C | 1 | W |
| dl/dt | Critical rate of rise of on-state current | $I_G = 2x I_{GT}$, $t_r \leq 100ns$ $f = 120$ Hz, $T_j = 125$ °C | 50 | $A/\mu s$ |
| T_j | Operating Temperature | | (-40 +125) | °C |
| T_{stg} | Storage Temperature | | (-40 +150) | °C |
| T_{sld} | Soldering Temperature | 10s max | 260 | °C |
| V_{iso} | R.M.S. isolation voltage 50/60 Hz sinusoidal waveform | | 2.500 | Vac |

| SYMBOL | PARAMETER | VOLTAGE | | | | | Unit |
|-----------|-----------------------------------|---------|-----|-----|-----|-----|------|
| | | B | D | M | S | N | |
| V_{DRM} | Repetitive Peak Off State Voltage | 200 | 400 | 600 | 700 | 800 | V |
| V_{RRM} | | | | | | | |

STANDARD TRIAC

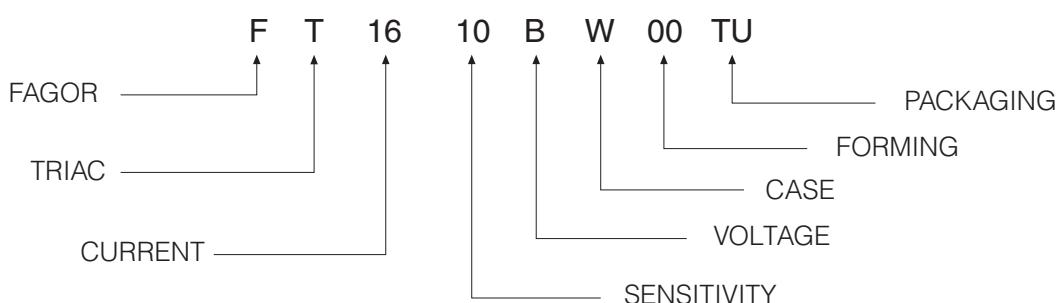
Electrical Characteristics

| SYMBOL | PARAMETER | CONDITIONS | Quadrant | SENSITIVITY | | | | Unit | |
|-------------------|---|---|----------|-------------|------|------|-----|------|------------------------|
| | | | | 10 | 13 | 18 | 17 | | |
| $I_{GT}^{(1)}$ | Gate Trigger Current | $V_D = 12 \text{ V}_{DC}$, $R_L = 33\Omega$, $T_j = 25^\circ\text{C}$ | Q1÷Q3 | MAX | 25 | 50 | 25 | 50 | mA |
| | | | Q4 | MAX | 25 | 75 | 50 | 100 | mA |
| V_{GT} | Gate Trigger Voltage | $V_D = 12 \text{ V}_{DC}$, $R_L = 33\Omega$, $T_j = 25^\circ\text{C}$ | Q1÷Q4 | MAX | 1.3 | | | | V |
| V_{GD} | Gate Non Trigger Voltage | $V_D = V_{DRM}$, $R_L = 3.3 \text{ K}\Omega$, $T_j = 125^\circ\text{C}$ | Q1÷Q4 | MIN | 0.2 | | | | V |
| $I_H^{(2)}$ | Holding Current | $I_T = 100 \text{ mA}$, Gate open, $T_j = 25^\circ\text{C}$ | | MAX | 25 | 50 | 25 | 50 | mA |
| I_L | Latching Current | $I_G = 1.2 I_{GT}$, $T_j = 25^\circ\text{C}$ | Q1,Q3,Q4 | MAX | 40 | 70 | 40 | 70 | mA |
| | | | Q2 | MAX | 60 | 80 | 80 | 100 | mA |
| $dV/dt^{(2)}$ | Critical Rate of Voltage Rise | $V_D = 0.67 \times V_{DRM}$, Gate open $T_j = 125^\circ\text{C}$ | | MIN | 500 | 1000 | 700 | 1000 | $\text{V}/\mu\text{s}$ |
| $(dV/dt)c^{(2)}$ | Critical Rise Rate of Commutating off-state voltage | $(dV/dt)c = 2.7 \text{ A/ms}$ $T_j = 125^\circ\text{C}$ | | MIN | 3 | 8 | 5 | 10 | $\text{V}/\mu\text{s}$ |
| $V_{TM}^{(2)}$ | On-state Voltage | $I_T = 22.5 \text{ Amp}$, $t_p = 380 \mu\text{s}$, $T_j = 25^\circ\text{C}$ | | MAX | 1.55 | | | | V |
| $V_{t(o)}^{(2)}$ | Threshold Voltage | $T_j = 125^\circ\text{C}$ | | MAX | 0.77 | | | | V |
| $r_d^{(2)}$ | Dynamic resistance | $T_j = 125^\circ\text{C}$ | | MAX | 30 | | | | $\text{m}\Omega$ |
| I_{DRM}/I_{RRM} | Off-State Leakage Current | $V_D = V_{DRM}$, $T_j = 125^\circ\text{C}$ | | MAX | 2 | | | | mA |
| | | $V_R = V_{RRM}$, $T_j = 25^\circ\text{C}$ | | MAX | 5 | | | | μA |
| $R_{th(j-c)}$ | Thermal Resistance Junction-Case | for AC 360° conduction angle | | | 2.7 | | | | $^\circ\text{C/W}$ |
| $R_{th(j-a)}$ | Thermal Resistance Junction-Ambient | | | | 50 | | | | $^\circ\text{C/W}$ |

(1) Minimum I_{GT} is guaranteed at 5% of I_{GT} max.

(2) For either polarity of electrode MT2 voltage with reference to electrode MT1.

PART NUMBER INFORMATION



STANDARD TRIAC

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle)

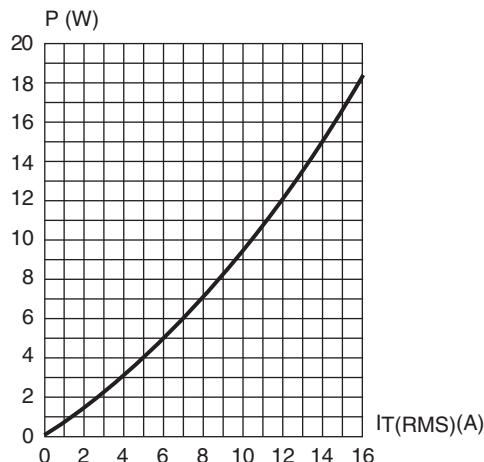


Fig. 2: RMS on-state current versus case temperature (full cycle).

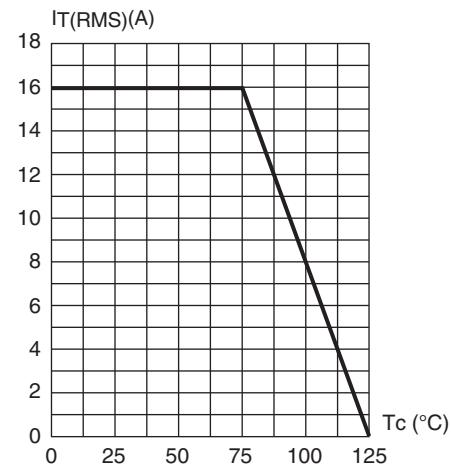


Fig. 3: Relative variation of thermal impedance versus pulse duration.

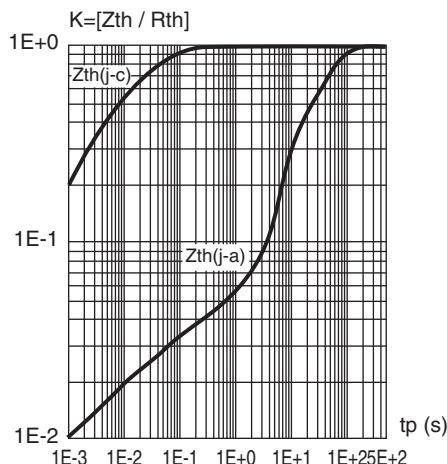


Fig. 5: Surge peak on-state current versus number of cycles

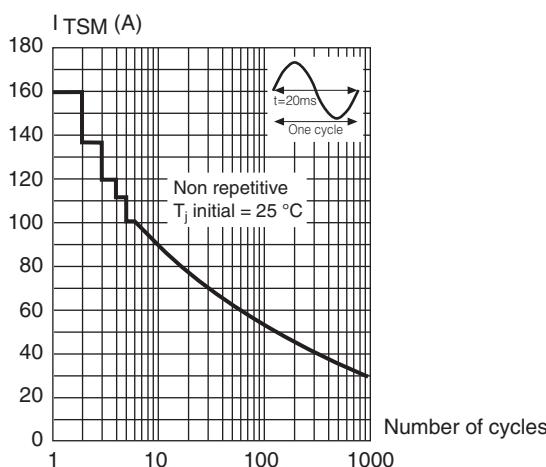


Fig. 4: On-state characteristics (maximum values)

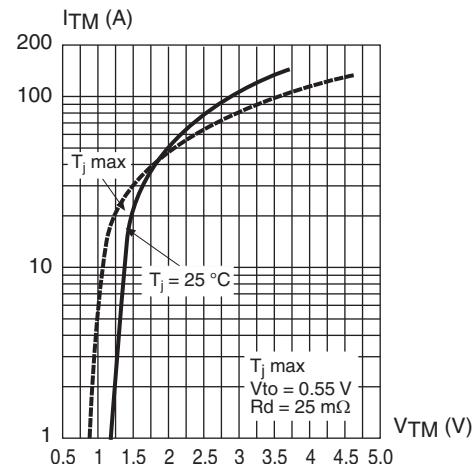
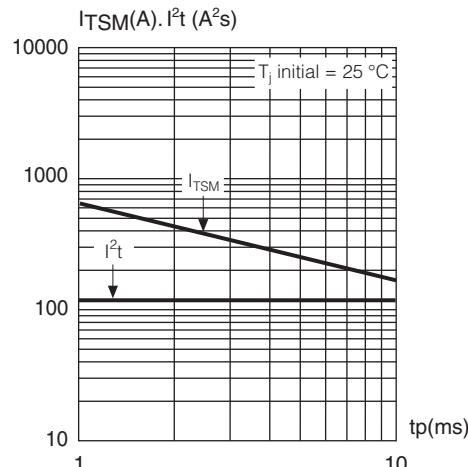


Fig. 6: Non repetitive surge peak on-state current for a sinusoidal pulse with width: tp < 10 ms, and corresponding value of I^2t .



STANDARD TRIAC

Fig. 7: Relative variation of gate trigger current, holding current and latching versus junction temperature (typical values)

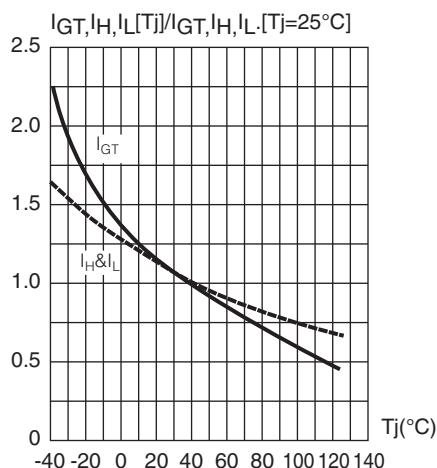


Fig. 8: Relative variation of critical rate of decrease of main current versus junction temperature

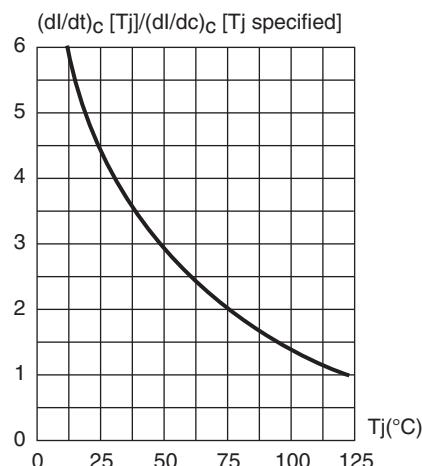
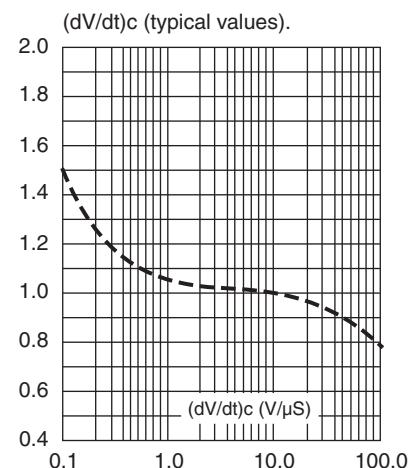


Fig. 9: Relative variation of critical rate of decrease of main current versus



PACKAGE MECHANICAL DATA

TO220-F

